

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	2	"6358800".pn.	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:06
2	BRS	12	("5434093" "5448094" "5668021" "5780340" "6033980" "6087208" "6100146" "6117712" "6130454" "6171916" "6204128" "6204133").PN.	USPAT	2004/09/12 19:06
3	BRS	1	"6358800".URPN.	USPAT	2004/09/12 19:08
4	BRS	9936	transistor with (recess trench)	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:47
5	BRS	1320	transistor with (recess trench) and etching with isolation	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:42
6	BRS	294	transistor near3 (recess trench) and etching near3 ((trench adj isolation) or (STI) or isolation or (field adj oxide))	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:47
7	BRS	11293	(gate transistor) near3 (recess trench)	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:47
8	BRS	622	((gate transistor) near3 (recess trench)) and etching near3 ((trench adj isolation) or (STI) or isolation or (field adj oxide))	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/12 19:49
9	BRS	42	((gate transistor) near3 (recess trench)) and etching near3 ((trench adj isolation) or (STI) or isolation or (field adj oxide)) same active adj region	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/09 18:57

	Type	Hits	Search Text	DBs	Time Stamp
10	BRS	758	257/328.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
11	BRS	611	257/329.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
12	BRS	984	257/330.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
13	BRS	342	257/332.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
14	BRS	188	257/334.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
15	BRS	781	257/336.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
16	BRS	239	257/337.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 19:20
17	BRS	1097	((gate transistor) near3 (recess trench)) and low\$3 near2 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/09 18:56

	Type	Hits	Search Text	DBs	Time Stamp
18	BRS	7	((gate transistor) near3 (recess trench)) and etching near3 ((trench adj isolation) or (STI) or isolation or (field adj oxide)) same active adj region and low\$3 near2 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/09 18:59
19	BRS	124	((gate transistor) near3 (recess trench)) and ((trench adj isolation) or (STI) or isolation or (field adj oxide)) same active adj region and low\$3 near2 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/09 19:00
20	BRS	83	((gate transistor) near3 (recess trench)) and ((trench adj isolation) or (STI) or isolation or (field adj oxide)) same active adj region and low\$3 near2 (source drain) and junction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/09 19:00
21	BRS	38	((gate transistor) near3 (recess trench)) and ((trench adj isolation) or (STI) or isolation or (field adj oxide)) same active adj region and low\$3 near2 (source drain) and junction and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/09 19:01
22	BRS	45	((gate transistor) near3 (recess trench)) and ((trench adj isolation) or (STI) or isolation or (field adj oxide)) same active adj region and low\$3 near2 (source drain) and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/09 19:01
23	BRS	725081	((gate transistor) near3 (recess trench)) and ((trench adj isolation) or (STI) or isolation or (field adj oxide)) same active adj region and low\$3 near2 (source drain) and spacer iwth (trench recess)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/09 19:01

	Type	Hits	Search Text	DBs	Time Stamp
24	BRS	19	((gate transistor) near3 (recess trench)) and ((trench adj isolation) or (STI) or isolation or (field adj oxide)) same active adj region and low\$3 near2 (source drain) and spacer with (trench recess)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/09 19:01
25	BRS	14	((gate transistor) near3 (recess trench)) and ((trench adj isolation) or (STI) or isolation or (field adj oxide)) same active adj region and low\$3 near2 (source drain) and junction and spacer with (trench recess)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/09 19:01